



Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
20V	190m Ω @4.5V	750mA
	260m Ω @2.5V	

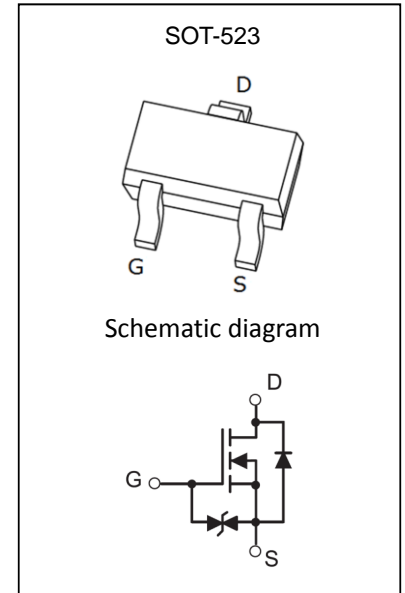
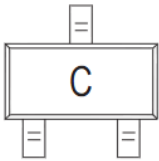
Feature

- High-Side Switching
- Low On-Resistance
- Low Threshold
- Fast Switching Speed
- ESD Protected

Application

- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories
- Battery Operated Systems
- Power Supply Converter Circuits
- Load/Power Switching Cell Phones, Pagers

MARKING:



ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	
Continuous Drain Current	I_D	750	mA
Pulsed Drain Current ¹	I_{DM}	1000	
Power Dissipation ²	P_D	150	mW
Maximum Power Dissipation ³		275	
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	833	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~ +150	

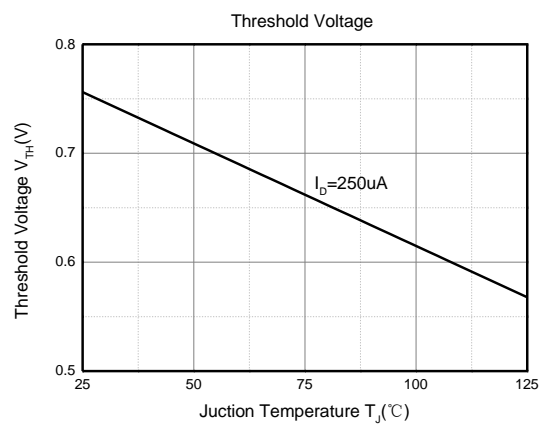
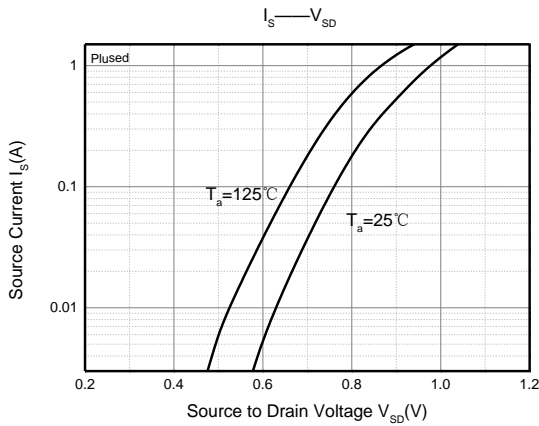
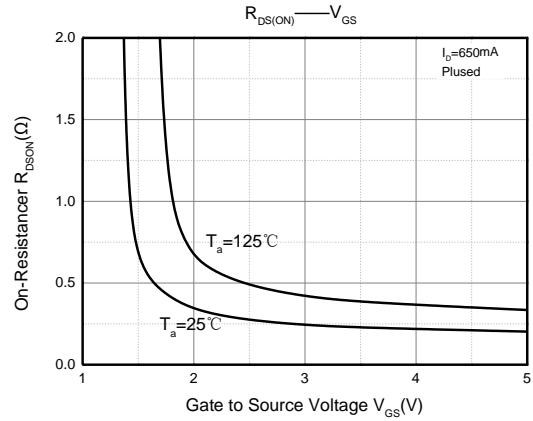
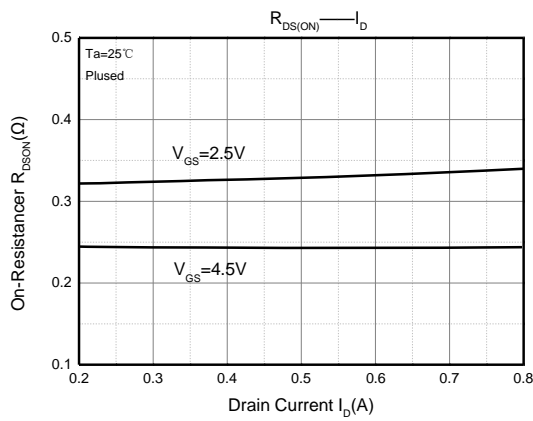
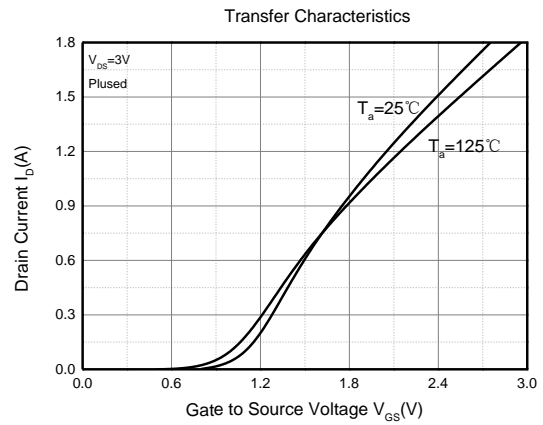
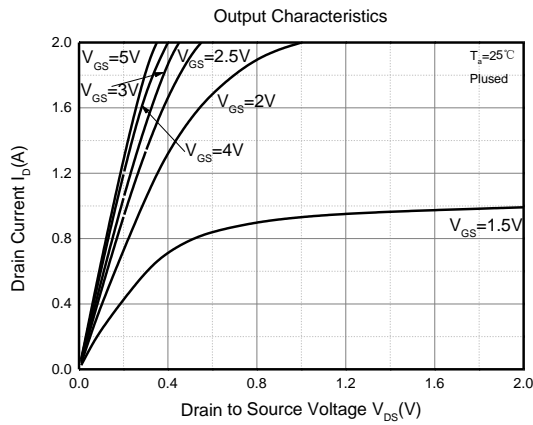
MOSFET ELECTRICAL CHARACTERISTICS(T_a=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =250μA	20			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =16V, V _{GS} = 0V			1	μA
Gate-body leakage current	I _{GSS}	V _{GS} =±4.5V, V _{DS} = 0V			±1	μA
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	0.45	0.7	1.2	V
Drain-source on-resistance	R _{DS(on)}	V _{GS} =4.5V, I _D =600mA		190	250	mΩ
		V _{GS} =2.5V, I _D =500mA		260	340	
Forward tranconductance	g _{FS}	V _{DS} =10V, I _D =400mA	1			S
Dynamic characteristics⁴						
Input Capacitance	C _{iss}	V _{DS} =16V, V _{GS} =0V, f =1MHz			120	pF
Output Capacitance	C _{oss}				20	
Reverse Transfer Capacitance	C _{rss}				15	
Switching Characteristics⁴						
Turn-on delay time	t _{d(on)}	V _{DD} =10V, I _D =500mA, V _{GS} =4.5V, R _G =10Ω		6.7		ns
Turn-on rise time	t _r			4.8		ns
Turn-off delay time	t _{d(off)}			17.3		ns
Turn-off fall time	t _f			7.4		ns
Source-Drain Diode characteristics						
Diode Forward voltage ⁵	V _{DS}	I _S =0.15A, V _{GS} = 0V			1.2	V

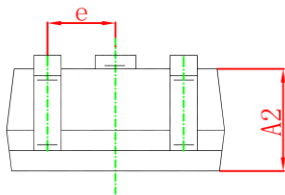
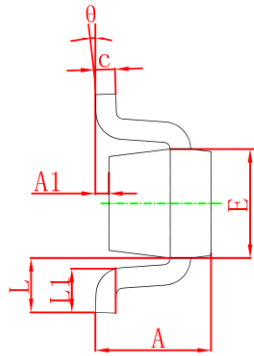
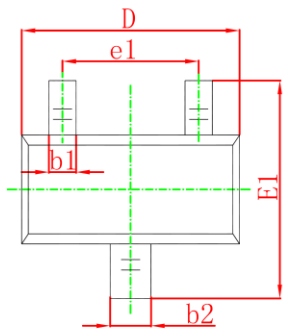
Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. This test is performed with no heat sink at Ta=25°C.
3. This test is performed with infinite heat sink at Tc=25°C.
4. These parameters have no way to verify.
5. Pulse Test : Pulse Width≤300μs, Duty Cycle≤0.5%.

Typical Electrical and Thermal Characteristics



SOT-523 Package Information

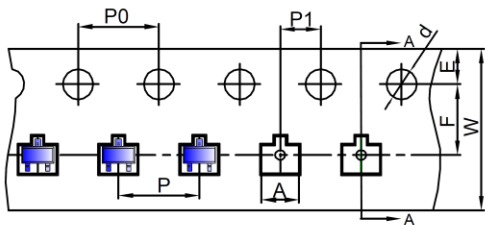


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500 TYP.		0.020 TYP.	
e1	0.900	1.100	0.035	0.043
L	0.400 REF.		0.016 REF.	
L1	0.260	0.460	0.010	0.018
theta	0°	8°	0°	8°

SOT-523 Tape and Reel

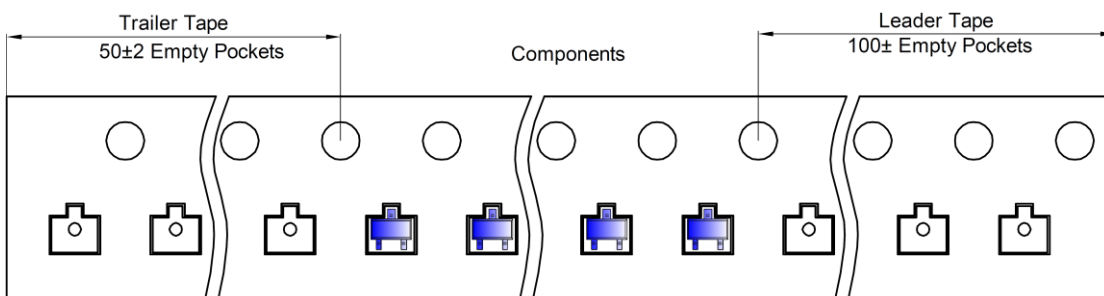
SOT-523 Tape and reel

SOT-523 Embossed Carrier Tape

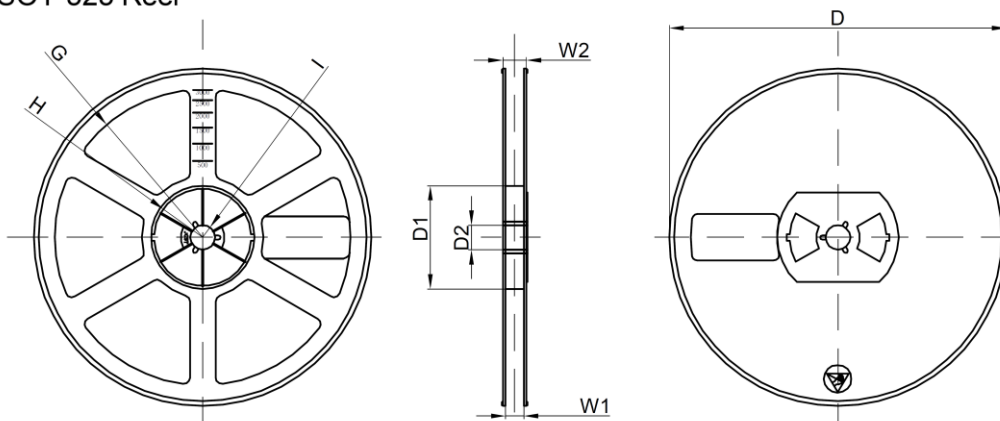


Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
SOT-523	1.85	1.85	0.875	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

SOT-523 Tape Leader and Trailer



SOT-523 Reel



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
7" Dia	Ø178.00	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3000 pcs	7 inch	30,000 pcs	203×203×195	120,000 pcs	438×438×220	